

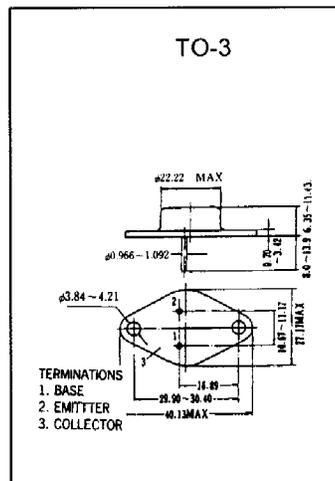
**MJ13335**

**NPN SILICON TRANSISTORS**

**HIGH VOLTAGE SILICON HIGH POWER TRANSISTORS**  
**SOLENOID AND RELAY DRIVERS**

**ABSOLUTE MAXIMUM RATINGS (Ta=25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	800	V
Collector-Emitter Voltage	V <sub>CE0</sub>	500	V
Collector Current (DC)	I <sub>C</sub>	20	A
Collector Dissipation (Tc=25°C)	P <sub>C</sub>	175	W
Junction Temperature	T <sub>J</sub>	200	°C
Storage Temperature	T <sub>stg</sub>	-50-150	°C



**ELECTRICAL CHARACTERISTICS (Ta=25°C)**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = 800V, I <sub>E</sub> =0			250	μA
Collector Cutoff Current	I <sub>CE0</sub>	V <sub>CB</sub> = 500V, I <sub>B</sub> =0			250	μA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = 5V, I <sub>C</sub> =5.0A	10		60	
Collector- Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =10A, I <sub>B</sub> =2A			1.8	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =10A, I <sub>B</sub> =2A			1.8	



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